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Applications of **Embedded - Microprocessors**

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e300c2
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	333MHz
Co-Processors/DSP	Communications; QUICC Engine, Security; SEC 2.2
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100Mbps (3)
SATA	-
USB	USB 2.0 (1)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	-40°C ~ 105°C (TA)
Security Features	Cryptography
Package / Case	516-BBGA
Supplier Device Package	516-PBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/kmpc8323ecvrafdc

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong





2.1.2 Power Supply Voltage Specification

Table 2 provides the recommended operating conditions for the MPC8323E. Note that these values are the recommended and tested operating conditions. Proper device operation outside of these conditions is not guaranteed.

Characteristic	Symbol	Recommended Value	Unit	Notes
Core supply voltage	V _{DD}	1.0 V ± 50 mV	V	1
PLL supply voltage	AV _{DD}	1.0 V ± 50 mV	V	1
DDR1 and DDR2 DRAM I/O voltage	GV _{DD}	2.5 V ± 125 mV 1.8 V ± 90 mV	V	1
PCI, local bus, DUART, system control and power management, I ² C, SPI, and JTAG I/O voltage	OV _{DD}	3.3 V ± 300 mV	V	1
Junction temperature	T _A /T _J	0 to 105	°C	2

Table 2. Recommended Operating Conditions³

Note:

1. GV_{DD}, OV_{DD}, AV_{DD}, and V_{DD} must track each other and must vary in the same direction—either in the positive or negative direction.

2. Minimum temperature is specified with T_A; maximum temperature is specified with T_J.

3. All IO pins should be interfaced with peripherals operating at same voltage level.

4. This voltage is the input to the filter discussed in Section 24.2, "PLL Power Supply Filtering" and not necessarily the voltage at the AVDD pin, which may be reduced due to voltage drop across the filter.

Figure 2 shows the undershoot and overshoot voltages at the interfaces of the MPC8323E



Figure 2. Overshoot/Undershoot Voltage for GV_{DD}/OV_{DD}



Electrical Characteristics

2.1.3 Output Driver Characteristics

Table 3 provides information on the characteristics of the output driver strengths. The values are preliminary estimates.

Driver Type	Output Impedance (Ω)	Supply Voltage
Local bus interface utilities signals	42	OV _{DD} = 3.3 V
PCI signals	25	
DDR1 signal	18	GV _{DD} = 2.5 V
DDR2 signal	18	GV _{DD} = 1.8 V
DUART, system control, I2C, SPI, JTAG	42	OV _{DD} = 3.3 V
GPIO signals	42	OV _{DD} = 3.3 V

Table 3. Output Drive Capability

2.1.4 Input Capacitance Specification

Table 4 describes the input capacitance for the CLKIN pin in the MPC8323E.

Table 4. Input Capacitance Specification

Parameter/Condition	Symbol	Min	Мах	Unit	Notes
Input capacitance for all pins except CLKIN	CI	6	8	pF	_
Input capacitance for CLKIN	C _{ICLKIN}	10		pF	1

Note:

1. The external clock generator should be able to drive 10 pF.

2.2 Power Sequencing

The device does not require the core supply voltage (V_{DD}) and IO supply voltages (GV_{DD}) and $OV_{DD})$ to be applied in any particular order. Note that during power ramp-up, before the power supplies are stable and if the I/O voltages are supplied before the core voltage, there might be a period of time that all input and output pins are actively driven and cause contention and excessive current. In order to avoid actively driving the I/O pins and to eliminate excessive current draw, apply the core voltage (V_{DD}) before the I/O voltage (GV_{DD}) and OV_{DD} and assert PORESET before the power supplies fully ramp up. In the case where the core voltage is applied first, the core voltage supply must rise to 90% of its nominal value before the I/O supplies reach 0.7 V; see Figure 3. Once both the power supplies (I/O voltage and core voltage) are stable, wait for a minimum of 32 clock cycles before negating PORESET.

Note that there is no specific power down sequence requirement for the device. I/O voltage supplies (GV_{DD}) and OV_{DD} do not have any ordering requirements with respect to one another.



Parameter/Condition	Min	Max	Unit	Notes
HRESET/SRESET assertion (output)	512	_	t _{PCI_SYNC_IN}	1
HRESET negation to SRESET negation (output)	16		t _{PCI_SYNC_IN}	1
Input setup time for POR configuration signals (CFG_RESET_SOURCE[0:2] and CFG_CLKIN_DIV) with respect to negation of PORESET when the MPC8323E is in PCI host mode	4	_	^t CLKIN	2
Input setup time for POR configuration signals (CFG_RESET_SOURCE[0:2] and CFG_CLKIN_DIV) with respect to negation of PORESET when the MPC8323E is in PCI agent mode	4	_	^t PCI_SYNC_IN	1
Input hold time for POR config signals with respect to negation of HRESET	0	_	ns	—
Time for the MPC8323E to turn off POR configuration signals with respect to the assertion of $\overrightarrow{\text{HRESET}}$	_	4	ns	3
Time for the MPC8323E to turn on POR configuration signals with respect to the negation of HRESET	1	_	^t PCI_SYNC_IN	1, 3

Table 9. RESET Initialization Timing Specifications (continued)

Notes:

1. t_{PCI_SYNC_IN} is the clock period of the input clock applied to PCI_SYNC_IN. When the MPC8323E is In PCI host mode the primary clock is applied to the CLKIN input, and PCI_SYNC_IN period depends on the value of CFG_CLKIN_DIV. See the *MPC8323E PowerQUICC II Pro Integrated Communications Processor Reference Manual* for more details.

 t_{CLKIN} is the clock period of the input clock applied to CLKIN. It is only valid when the MPC8323E is in PCI host mode. See the MPC8323E PowerQUICC II Pro Integrated Communications Processor Reference Manual for more details.

3. POR configuration signals consists of CFG_RESET_SOURCE[0:2] and CFG_CLKIN_DIV.

Table 10 provides the PLL lock times.

Table 10. PLL Lock Times

Parameter/Condition	Min	Мах	Unit	Notes
PLL lock times		100	μs	_

5.1 Reset Signals DC Electrical Characteristics

Table 11 provides the DC electrical characteristics for the MPC8323E reset signals mentioned in Table 9.

Table 11. Reset Signals DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Мах	Unit	Notes
Output high voltage	V _{OH}	I _{OH} = -6.0 mA	2.4	—	V	1
Output low voltage	V _{OL}	I _{OL} = 6.0 mA	—	0.5	V	1
Output low voltage	V _{OL}	I _{OL} = 3.2 mA	—	0.4	V	1
Input high voltage	V _{IH}	—	2.0	OV _{DD} + 0.3	V	1
Input low voltage	V _{IL}	_	-0.3	0.8	V	_



DDR1 and DDR2 SDRAM

Table 13. DDR2 SDRAM Capacitance for Dn_GV_{DD}(typ) = 1.8 V

Delta input/output capacitance: DQ, DQS	C _{DIO}	-	0.5	pF	1

Note:

1. This parameter is sampled. $Dn_GV_{DD} = 1.8 \text{ V} \pm 0.090 \text{ V}$, f = 1 MHz, T_A = 25 °C, V_{OUT} = $Dn_GV_{DD} \div 2$,

V_{OUT} (peak-to-peak) = 0.2 V.

Table 14 provides the recommended operating conditions for the DDR1 SDRAM component(s) of the MPC8323E when $Dn_GV_{DD}(typ) = 2.5 V.$

Parameter/Condition Symbol Min Max Unit Notes V I/O supply voltage 2.375 2.625 Dn_GV_{DD} 1 I/O reference voltage MVREF n_{REF} $0.49 \times Dn_GV_{DD}$ $0.51 \times Dn_GV_{DD}$ V 2 I/O termination voltage MVREF n_{REF} - 0.04 MVREFn_{REF} + 0.04 ٧ 3 VTT Input high voltage VIH MVREFn_{REF} + 0.15 $Dn_GV_{DD} + 0.3$ ٧ ٧ Input low voltage VIL -0.3 MVREFn_{REF} – 0.15 Output leakage current -9.9 loz -9.9 μΑ 4 Output high current (V_{OUT} = 1.95 V) -16.2 mΑ I_{OH} Output low current (V_{OUT} = 0.35 V) 16.2 mΑ I_{OL}

Table 14. DDR1 SDRAM DC Electrical Characteristics for Dn_GV_{DD}(typ) = 2.5 V

Notes:

1. Dn_GV_{DD} is expected to be within 50 mV of the DRAM Dn_GV_{DD} at all times.

2. MVREF n_{BEF} is expected to be equal to $0.5 \times Dn_{\text{GV}DD}$, and to track $Dn_{\text{GV}DD}$ DC variations as measured at the receiver. Peak-to-peak noise on MVREF nREF may not exceed ±2% of the DC value.

3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MVREFn_{REF}. This rail should track variations in the DC level of MVREFn_{REF}.

4. Output leakage is measured with all outputs disabled, $0 V \le V_{OUT} \le Dn_GV_{DD}$.

Table 15 provides the DDR1 capacitance $Dn_GV_{DD}(typ) = 2.5$ V.

Table 15. DDR1 SDRAM Capacitance for Dn_GV_{DD}(typ) = 2.5 V Interface

Parameter/Condition	Symbol	Min	Мах	Unit	Notes
Input/output capacitance: DQ,DQS	C _{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS	C _{DIO}		0.5	pF	1

Note:

1. This parameter is sampled. $Dn_GV_{DD} = 2.5 V \pm 0.125 V$, f = 1 MHz, $T_A = 25^{\circ} C$, $V_{OUT} = Dn_GV_{DD} \div 2$, V_{OUT} (peak-to-peak) = 0.2 V.



6.2 DDR1 and DDR2 SDRAM AC Electrical Characteristics

This section provides the AC electrical characteristics for the DDR1 and DDR2 SDRAM interface.

6.2.1 DDR1 and DDR2 SDRAM Input AC Timing Specifications

Table 16 provides the input AC timing specifications for the DDR2 SDRAM ($Dn_GV_{DD}(typ) = 1.8 \text{ V}$).

Table 16. DDR2 SDRAM Input AC Timing Specifications for 1.8-V Interface

At recommended operating conditions with Dn_GV_{DD} of 1.8 ± 5%.

Parameter	Symbol	Min	Мах	Unit	Notes
AC input low voltage	V _{IL}	—	MVREF <i>n</i> _{REF} – 0.25	V	—
AC input high voltage	V _{IH}	MVREFn _{REF} + 0.25	_	V	

Table 17 provides the input AC timing specifications for the DDR1 SDRAM ($Dn_GV_{DD}(typ) = 2.5 V$).

Table 17. DDR1 SDRAM Input AC Timing Specifications for 2.5 V Interface

At recommended operating conditions with Dn_GV_{DD} of 2.5 ± 5%.

Parameter	Symbol	Min	Мах	Unit	Notes
AC input low voltage	V _{IL}	—	MVREF <i>n</i> _{REF} – 0.31	V	
AC input high voltage	V _{IH}	MVREF <i>n</i> _{REF} + 0.31	_	V	

Table 18 provides the input AC timing specifications for the DDR1 and DDR2 SDRAM interface.

Table 18. DDR1 and DDR2 SDRAM Input AC Timing Specifications

At recommended operating conditions with Dn_GV_{DD} of (1.8 or 2.5 V) ± 5%.

Parameter	Symbol	Min	Мах	Unit	Notes
Controller skew for MDQS—MDQ/MDM 266 MHz 200 MHz	^t CISKEW	-750 -1250	750 1250	ps	1, 2

Notes:

1. t_{CISKEW} represents the total amount of skew consumed by the controller between MDQS[n] and any corresponding bit that is captured with MDQS[n]. This should be subtracted from the total timing budget.

 The amount of skew that can be tolerated from MDQS to a corresponding MDQ signal is called t_{DISKEW}. This can be determined by the following equation: t_{DISKEW} = ±(T/4 – abs(t_{CISKEW})) where T is the clock period and abs(t_{CISKEW}) is the absolute value of t_{CISKEW}.



DDR1 and DDR2 SDRAM

Figure 4 shows the input timing diagram for the DDR controller.



Figure 4. DDR Input Timing Diagram

6.2.2 DDR1 and DDR2 SDRAM Output AC Timing Specifications

Table 19 provides the output AC timing specifications for the DDR1 and DDR2 SDRAM interfaces.

Table 19. DDR1 and DDR2 SDRAM Output AC Timing Specifications

At recommended operating conditions with Dn_GV_{DD} of (1.8 or 2.5 V) \pm 5%.

Parameter	Symbol ¹	Min	Мах	Unit	Notes
MCK cycle time, (MCK/MCK crossing)	t _{MCK}	7.5	10	ns	2
ADDR/CMD output setup with respect to MCK 266 MHz 200 MHz	^t DDKHAS	2.5 3.5		ns	3
ADDR/CMD output hold with respect to MCK 266 MHz 200 MHz	t _{DDKHAX}	2.5 3.5		ns	3
MCS output setup with respect to MCK 266 MHz 200 MHz	t _{DDKHCS}	2.5 3.5		ns	3
MCS output hold with respect to MCK 266 MHz 200 MHz	^t DDKHCX	2.5 3.5		ns	3
MCK to MDQS Skew	t _{DDKHMH}	-0.6	0.6	ns	4



7 DUART

This section describes the DC and AC electrical specifications for the DUART interface of the MPC8323E.

7.1 DUART DC Electrical Characteristics

Table 20 provides the DC electrical characteristics for the DUART interface of the MPC8323E.

Table 20. DUART DC Electrical Characteristics

Parameter	Symbol	Min	Мах	Unit
High-level input voltage	V _{IH}	2	OV _{DD} + 0.3	V
Low-level input voltage OV _{DD}	V _{IL}	-0.3	0.8	V
High-level output voltage, $I_{OH} = -100 \ \mu A$	V _{OH}	OV _{DD} – 0.2	—	V
Low-level output voltage, $I_{OL} = 100 \ \mu A$	V _{OL}	—	0.2	V
Input current (0 V \leq V _{IN} \leq OV _{DD}) ¹	I _{IN}	—	±5	μA

Note:

1. Note that the symbol V_{IN} , in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

7.2 DUART AC Electrical Specifications

Table 21 provides the AC timing parameters for the DUART interface of the MPC8323E.

Table 21	. DUART	AC Timing	Specifications
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Parameter	Value	Unit	Notes
Minimum baud rate	256	baud	
Maximum baud rate	> 1,000,000	baud	1
Oversample rate	16		2

Notes:

1. Actual attainable baud rate is limited by the latency of interrupt processing.

2. The middle of a start bit is detected as the 8th sampled 0 after the 1-to-0 transition of the start bit. Subsequent bit values are sampled each 16th sample.

8 Ethernet and MII Management

This section provides the AC and DC electrical characteristics for Ethernet and MII management.

8.1 Ethernet Controller (10/100 Mbps)—MII/RMII Electrical Characteristics

The electrical characteristics specified here apply to all MII (media independent interface) and RMII (reduced media independent interface), except MDIO (management data input/output) and MDC



Local Bus

Figure 13 shows the MII management AC timing diagram.



Figure 13. MII Management Interface Timing Diagram

9 Local Bus

This section describes the DC and AC electrical specifications for the local bus interface of the MPC8323E.

9.1 Local Bus DC Electrical Characteristics

Table 29 provides the DC electrical characteristics for the local bus interface.

Table 29. Local Bus DC Electrical Characteristics

Parameter	Symbol	Min	Мах	Unit
High-level input voltage	V _{IH}	2	OV _{DD} + 0.3	V
Low-level input voltage	V _{IL}	-0.3	0.8	V
High-level output voltage, I _{OH} = −100 μA	V _{OH}	OV _{DD} – 0.2	—	V
Low-level output voltage, I _{OL} = 100 μA	V _{OL}	—	0.2	V
Input current	I _{IN}	—	±5	μA

9.2 Local Bus AC Electrical Specifications

Table 30 describes the general timing parameters of the local bus interface of the MPC8323E.

Table 30. Local Bus General Timing Parameters

Parameter	Symbol ¹	Min	Мах	Unit	Notes
Local bus cycle time	t _{LBK}	15	—	ns	2
Input setup to local bus clock (LCLKn)	t _{LBIVKH}	7	—	ns	3, 4
Input hold from local bus clock (LCLKn)	t _{LBIXKH}	1.0	—	ns	3, 4
LALE output fall to LAD output transition (LATCH hold time)	t _{LBOTOT1}	1.5	—	ns	5



Figure 15 through Figure 17 show the local bus signals.





JTAG

Table 31. JTAG Interface DC Electrical Characteristics (continued)
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Characteristic	Symbol	Condition	Min	Мах	Unit
Input low voltage	V _{IL}	—	-0.3	0.8	V
Input current	I _{IN}	$0~V \leq V_{IN} \leq OV_{DD}$	—	±5	μA

10.2 JTAG AC Electrical Characteristics

This section describes the AC electrical specifications for the IEEE Std. 1149.1 (JTAG) interface of the MPC8323E. Table 32 provides the JTAG AC timing specifications as defined in Figure 19 through Figure 22.

Table 32. JTAG AC Timing Specifications (Independent of CLKIN)¹

At recommended operating conditions (see Table 2).

Parameter	Symbol ²	Min	Мах	Unit	Notes
JTAG external clock frequency of operation	f _{JTG}	0	33.3	MHz	
JTAG external clock cycle time	t _{JTG}	30	_	ns	_
JTAG external clock pulse width measured at 1.4 V	t _{JTKHKL}	11	—	ns	—
JTAG external clock rise and fall times	t _{JTGR} , t _{JTGF}	0	2	ns	—
TRST assert time	t _{TRST}	25	—	ns	3
Input setup times: Boundary-scan data TMS, TDI	t _{JTDVKH} t _{JTIVKH}	4 4		ns	4
Input hold times: Boundary-scan data TMS, TDI	^t jtdxkh t _{jtixkh}	10 10		ns	4
Valid times: Boundary-scan data TDO	tjtkldv tjtklov	2 2	15 15	ns	5
Output hold times: Boundary-scan data TDO	t _{jtkldx} t _{jtklox}	2 2	_	ns	5



Figure 21 provides the boundary-scan timing diagram.



Figure 21. Boundary-Scan Timing Diagram





Figure 22. Test Access Port Timing Diagram



11 I²C

This section describes the DC and AC electrical characteristics for the I²C interface of the MPC8323E.

11.1 I²C DC Electrical Characteristics

Table 33 provides the DC electrical characteristics for the I²C interface of the MPC8323E.

Table 33. I²C DC Electrical Characteristics

At recommended operating conditions with OV_{DD} of 3.3 V \pm 10%.

Parameter	Symbol	Min	Мах	Unit	Notes
Input high voltage level	V _{IH}	$0.7 imes OV_{DD}$	OV _{DD} + 0.3	V	
Input low voltage level	V _{IL}	-0.3	$0.3\times\text{OV}_{\text{DD}}$	V	_
Low level output voltage	V _{OL}	0	0.4	V	1
Output fall time from $V_{IH}(min)$ to $V_{IL}(max)$ with a bus capacitance from 10 to 400 pF	^t I2KLKV	$20 + 0.1 \times C_B$	250	ns	2
Pulse width of spikes which must be suppressed by the input filter	t _{I2KHKL}	0	50	ns	3
Capacitance for each I/O pin	Cl	_	10	pF	_
Input current (0 V \leq V _{IN} \leq OV _{DD})	I _{IN}	—	±5	μA	4

Notes:

1. Output voltage (open drain or open collector) condition = 3 mA sink current.

2. C_B = capacitance of one bus line in pF.

3. Refer to the MPC8323E PowerQUICC II Pro Integrated Communications Processor Reference Manual for information on the digital filter used.

4. I/O pins obstructs the SDA and SCL lines if $\ensuremath{\mathsf{OV}_{\mathsf{DD}}}$ is switched off.

11.2 I²C AC Electrical Specifications

Table 34 provides the AC timing parameters for the I^2C interface of the MPC8323E.

Table 34. I²C AC Electrical Specifications

All values refer to V_{IH} (min) and V_{IL} (max) levels (see Table 33).

Parameter	Symbol ¹	Min	Мах	Unit
SCL clock frequency	f _{I2C}	0	400	kHz
Low period of the SCL clock		1.3	—	μs
High period of the SCL clock		0.6	—	μs
Setup time for a repeated START condition		0.6	—	μs
Hold time (repeated) START condition (after this period, the first clock pulse is generated)		0.6	_	μs
Data setup time	t _{i2DVKH}	100	—	ns
Data hold time: CBUS compatible masters I ² C bus devices	t _{I2DXKL}	$\overline{0^2}$	 0.9 ³	μs



12 PCI

This section describes the DC and AC electrical specifications for the PCI bus of the MPC8323E.

12.1 PCI DC Electrical Characteristics

Table 35 provides the DC electrical characteristics for the PCI interface of the MPC8323E.

Parameter	Symbol	Test Condition	Min	Мах	Unit
High-level input voltage	V _{IH}	$V_{OUT} \ge V_{OH}$ (min) or	2	OV _{DD} + 0.3	V
Low-level input voltage	V _{IL}	$V_{OUT} \le V_{OL}$ (max)	-0.3	0.8	V
High-level output voltage	V _{OH}	OV _{DD} = min, I _{OH} = −100 μA	OV _{DD} – 0.2	—	V
Low-level output voltage	V _{OL}	OV _{DD} = min, I _{OL} = 100 μA	_	0.2	V
Input current	I _{IN}	$0 V \le V_{IN} \le OV_{DD}$	_	±5	μA

Table 35. PCI DC Electrical Characteristics^{1,2}

Notes:

1. Note that the symbol V_{IN} , in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

2. Ranges listed do not meet the full range of the DC specifications of the PCI 2.3 Local Bus Specifications.

12.2 PCI AC Electrical Specifications

This section describes the general AC timing parameters of the PCI bus of the MPC8323E. Note that the PCI_CLK or PCI_SYNC_IN signal is used as the PCI input clock depending on whether the MPC8323E is configured as a host or agent device. Table 36 shows the PCI AC timing specifications at 66 MHz.

Parameter	Symbol ¹	Min	Max	Unit	Notes
Clock to output valid	t _{PCKHOV}	_	6.0	ns	2
Output hold from clock	t _{PCKHOX}	1	_	ns	2
Clock to output high impedence	t _{PCKHOZ}	_	14	ns	2, 3
Input setup to clock	t _{PCIVKH}	3.0	_	ns	2, 4
Input hold from clock	t _{PCIXKH}	0	—	ns	2, 4

Table 36. PCI AC Timing Specifications at 66 MHz

Notes:

The symbols used for timing specifications follow the pattern of t<sub>(first two letters of functional block)(signal)(state)(reference)(state) for inputs and t_{(first two letters of functional block)(reference)(state)(signal)(state)} for outputs. For example, t_{PCIVKH} symbolizes PCI timing (PC) with respect to the time the input signals (I) reach the valid state (V) relative to the PCI_SYNC_IN clock, t_{SYS}, reference (K) going to the high (H) state or setup time. Also, t_{PCRHFV} symbolizes PCI timing (PC) with respect to the time hard reset (R) went high (H) relative to the frame signal (F) going to the valid (V) state.
</sub>

- 2. See the timing measurement conditions in the PCI 2.3 Local Bus Specifications.
- 3. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
- 4. Input timings are measured at the pin.



Figure 31 and Figure 32 represent the AC timing from Table 45. Note that although the specifications generally reference the rising edge of the clock, these AC timing diagrams also apply when the falling edge is the active edge.

Figure 31 shows the SPI timing in slave mode (external clock).



Note: The clock edge is selectable on SPI.

Figure 31. SPI AC Timing in Slave Mode (External Clock) Diagram

Figure 32 shows the SPI timing in master mode (internal clock).



Note: The clock edge is selectable on SPI.

Figure 32. SPI AC Timing in Master Mode (Internal Clock) Diagram

17 TDM/SI

This section describes the DC and AC electrical specifications for the time-division-multiplexed and serial interface of the MPC8323E.

17.1 TDM/SI DC Electrical Characteristics

Table 46 provides the DC electrical characteristics for the MPC8323E TDM/SI.

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	V _{OH}	I _{OH} = -2.0 mA	2.4	_	V
Output low voltage	V _{OL}	I _{OL} = 3.2 mA	_	0.5	V
Input high voltage	V _{IH}	—	2.0	OV _{DD} + 0.3	V

Table 46. TDM/SI DC Electrical Characteristics



Package and Pin Listings

Signal	Signal Package Pin Number		Power Supply	Notes
MEMC_MDQ29	AD20	AD20 IO		
MEMC_MDQ30	AF23	AF23 IO		
MEMC_MDQ31	AD22	IO	GV _{DD}	—
MEMC_MDM0	AC9	0	GV _{DD}	—
MEMC_MDM1	AD5	0	GV _{DD}	—
MEMC_MDM2	AE20	AE20 O G		—
MEMC_MDM3	AE22	0	GV _{DD}	—
MEMC_MDQS0	AE8	IO	GV _{DD}	—
MEMC_MDQS1	AE5	IO	GV _{DD}	—
MEMC_MDQS2	AC19	IO	GV _{DD}	—
MEMC_MDQS3	AE23	IO	GV _{DD}	—
MEMC_MBA0	AD16	0	GV _{DD}	—
MEMC_MBA1	AD17	0	GV _{DD}	—
MEMC_MBA2	AE17	0	GV _{DD}	—
MEMC_MA0	AD12	0	GV _{DD}	—
MEMC_MA1	AE12	AE12 O		—
MEMC_MA2	AF12	0	GV _{DD}	—
MEMC_MA3	AC13	0	GV _{DD}	—
MEMC_MA4	AD13	0	GV _{DD}	—
MEMC_MA5	AE13	0	GV _{DD}	—
MEMC_MA6	AF13	0	GV _{DD}	—
MEMC_MA7	AC15	0	GV _{DD}	—
MEMC_MA8	AD15	0	GV _{DD}	—
MEMC_MA9	AE15	0	GV _{DD}	—
MEMC_MA10	AF15	0	GV _{DD}	—
MEMC_MA11	AE16	0	GV _{DD}	—
MEMC_MA12	AF16	0	GV _{DD}	—
MEMC_MA13	AB16 O G		GV _{DD}	—
MEMC_MWE	AC17 O		GV _{DD}	—
MEMC_MRAS	AE11 O		GV _{DD}	[_
MEMC_MCAS	AD11	0	GV _{DD}	[_
MEMC_MCS	AC11	0	GV _{DD}	_

Table 55. MPC8323E PBGA Pinout Listing (continued)



Package and Pin Listings

Table 55. MPC8323E PBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes			
Power and Ground Supplies							
AV _{DD} 1	P3	I	AV _{DD} 1	_			
AV _{DD} 2	AA1	I	AV _{DD} 2	_			
AV _{DD} 3	AB15	I	AV _{DD} 3	_			
AV _{DD} 4	C24	I	AV _{DD} 4	_			
MVREF1	AB8	I	DDR reference voltage	_			
MVREF2	AB17	I	DDR reference voltage	_			
	PCI						
PCI_INTA /IRQ_OUT	AF2	0	OV _{DD}	2			
PCI_RESET_OUT	AE2	0	OV _{DD}	_			
PCI_AD0/MSRCID0 (DDR ID)	L1	IO	OV _{DD}	_			
PCI_AD1/MSRCID1 (DDR ID)	L2	IO	OV _{DD}	_			
PCI_AD2/MSRCID2 (DDR ID)	M1	IO	OV _{DD}	_			
PCI_AD3/MSRCID3 (DDR ID)	M2	IO	OV _{DD}	_			
PCI_AD4/MSRCID4 (DDR ID)	L3	IO	OV _{DD}	_			
PCI_AD5/MDVAL (DDR ID)	N1	Ю	OV _{DD}				
PCI_AD6	N2	Ю	OV _{DD}				
PCI_AD7	МЗ	Ю	OV _{DD}				
PCI_AD8	P1	Ю	OV _{DD}				
PCI_AD9	R1	Ю	OV_{DD}				
PCI_AD10	N3	Ю	OV _{DD}				
PCI_AD11	N4	Ю	OV _{DD}				
PCI_AD12	T1	Ю	OV _{DD}				
PCI_AD13	R2	Ю	OV _{DD}				
PCI_AD14/ECID_TMODE_IN	T2	Ю	OV _{DD}				
PCI_AD15	U1	IO	OV _{DD}	_			
PCI_AD16	Y2	IO	OV _{DD}				
PCI_AD17	¥1	IO	OV _{DD}	_			
PCI_AD18	AA2	IO	OV _{DD}				
PCI_AD19	AB1	IO	OV _{DD}	_			



Signal	Package Pin Number	Pin Type	Power Supply	Notes
PCI_AD20	AB2	IO	OV _{DD}	—
PCI_AD21	Y4	IO	OV _{DD}	—
PCI_AD22	AC1	IO	OV _{DD}	—
PCI_AD23	AA3	IO	OV _{DD}	—
PCI_AD24	AA4	IO	OV _{DD}	—
PCI_AD25	AD1	Ю	OV _{DD}	
PCI_AD26	AD2	Ю	OV _{DD}	
PCI_AD27	AB3	IO	OV _{DD}	—
PCI_AD28	AB4	IO	OV _{DD}	—
PCI_AD29	AE1	IO	OV _{DD}	—
PCI_AD30	AC3	IO	OV _{DD}	
PCI_AD31	AC4	IO	OV _{DD}	—
PCI_C_BE0	M4	IO	OV _{DD}	—
PCI_C_BE1	T4	IO	OV _{DD}	—
PCI_C_BE2	Y3	IO	OV _{DD}	—
PCI_C_BE3	AC2	IO	OV _{DD}	—
PCI_PAR	U3	IO	OV _{DD}	—
PCI_FRAME	W1	IO	OV _{DD}	5
PCI_TRDY	W4	IO	OV _{DD}	5
PCI_IRDY	W2	IO	OV _{DD}	5
PCI_STOP	V4	IO	OV _{DD}	5
PCI_DEVSEL	W3	IO	OV _{DD}	5
PCI_IDSEL	P2	I	OV _{DD}	—
PCI_SERR	U4	IO	OV _{DD}	5
PCI_PERR	V3	IO	OV _{DD}	5
PCI_REQ0	AD4	IO	OV _{DD}	—
PCI_REQ1/CPCI_HS_ES	AE3	I	OV _{DD}	—
PCI_REQ2	AF3	I	OV _{DD}	—
PCI_GNT0	AD3	IO	OV _{DD}	—
PCI_GNT1/CPCI_HS_LED	AE4	0	OV _{DD}	—
PCI_GNT2/CPCI_HS_ENUM	AF4	0	OV _{DD}	—
M66EN	L4	I	OV _{DD}	—

Table 55. MPC8323E PBGA Pinout Listing (continued)



Signal	Package Pin Number	Pin Type	Power Supply	Notes
GPIO_PA26/Enet2_RX_ER/SER2_CD/TDMB_REQ/ LA10 (LBIU)	E26	IO	OV _{DD}	—
GPIO_PA27/Enet2_TX_ER/TDMB_CLKO/LA11 (LBIU)	F25	IO	OV _{DD}	—
GPIO_PA28/Enet2_RX_DV/SER2_CTS/ TDMB_RSYNC/LA12 (LBIU)	E25	IO	OV _{DD}	—
GPIO_PA29/Enet2_COL/RXD[4]/SER2_RXD[4]/ TDMB_STROBE/LA13 (LBIU)	J25	IO	OV _{DD}	—
GPIO_PA30/Enet2_TX_EN/SER2_RTS/ TDMB_TSYNC/LA14 (LBIU)	F26	IO	OV _{DD}	—
GPIO_PA31/Enet2_CRS/SDET LA15 (LBIU)	J26	IO	OV _{DD}	—
GPIO_PB0/Enet3_TXD[0]/SER3_TXD[0]/ TDMC_TXD[0]	A13	IO	OV _{DD}	—
GPIO_PB1/Enet3_TXD[1]/SER3_TXD[1]/ TDMC_TXD[1]	B13	IO	OV _{DD}	—
GPIO_PB2/Enet3_TXD[2]/SER3_TXD[2]/ TDMC_TXD[2]	A14	IO	OV _{DD}	—
GPIO_PB3/Enet3_TXD[3]/SER3_TXD[3]/ TDMC_TXD[3]	B14	IO	OV _{DD}	
GPIO_PB4/Enet3_RXD[0]/SER3_RXD[0]/ TDMC_RXD[0]	B8	IO	OV _{DD}	_
GPIO_PB5/Enet3_RXD[1]/SER3_RXD[1]/ TDMC_RXD[1]	A8	IO	OV _{DD}	
GPIO_PB6/Enet3_RXD[2]/SER3_RXD[2]/ TDMC_RXD[2]	A9	IO	OV _{DD}	
GPIO_PB7/Enet3_RXD[3]/SER3_RXD[3]/ TDMC_RXD[3]	В9	IO	OV _{DD}	_
GPIO_PB8/Enet3_RX_ER/SER3_CD/TDMC_REQ	A11	IO	OV _{DD}	—
GPIO_PB9/Enet3_TX_ER/TDMC_CLKO	B11	IO	OV _{DD}	—
GPIO_PB10/Enet3_RX_DV/SER3_CTS/ TDMC_RSYNC	A10	IO	OV _{DD}	
GPIO_PB11/Enet3_COL/RXD[4]/SER3_RXD[4]/ TDMC_STROBE	A15	IO	OV _{DD}	_
GPIO_PB12/Enet3_TX_EN/SER3_RTS/ TDMC_TSYNC	B12	IO	OV _{DD}	_
GPIO_PB13/Enet3_CRS/SDET	B15	IO	OV _{DD}	—
GPIO_PB14/CLK12	D9	IO	OV _{DD}	—
GPIO_PB15 UPC1_TxADDR[4]	D14	IO	OV _{DD}	—
GPIO_PB16 UPC1_RxADDR[4]	B16	IO	OV _{DD}	—

Table 55. MPC8323E PBGA Pinout Listing (continued)



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interface. From this case temperature, the junction temperature is determined from the junction-to-case thermal resistance.

$$T_J = T_C + (R_{\theta JC} \times P_D)$$

where:

 T_C = case temperature of the package (°C) $R_{\theta JC}$ = junction-to-case thermal resistance (°C/W) P_D = power dissipation (W)

24 System Design Information

This section provides electrical and thermal design recommendations for successful application of the MPC8323E.

24.1 System Clocking

The MPC8323E includes three PLLs.

- The system PLL (AV_{DD}2) generates the system clock from the externally supplied CLKIN input. The frequency ratio between the system and CLKIN is selected using the system PLL ratio configuration bits as described in Section 22.4, "System PLL Configuration."
- The e300 core PLL (AV_{DD}3) generates the core clock as a slave to the system clock. The frequency ratio between the e300 core clock and the system clock is selected using the e300 PLL ratio configuration bits as described in Section 22.5, "Core PLL Configuration."
- The QUICC Engine PLL (AV_{DD}1) which uses the same reference as the system PLL. The QUICC Engine block generates or uses external sources for all required serial interface clocks.

24.2 PLL Power Supply Filtering

Each of the PLLs listed above is provided with power through independent power supply pins. The voltage level at each $AV_{DD}n$ pin should always be equivalent to V_{DD} , and preferably these voltages are derived directly from V_{DD} through a low frequency filter scheme such as the following.

There are a number of ways to reliably provide power to the PLLs, but the recommended solution is to provide five independent filter circuits as illustrated in Figure 44, one to each of the five AV_{DD} pins. By providing independent filters to each PLL the opportunity to cause noise injection from one PLL to the other is reduced.

This circuit is intended to filter noise in the PLLs resonant frequency range from a 500 kHz to 10 MHz range. It should be built with surface mount capacitors with minimum effective series inductance (ESL). Consistent with the recommendations of Dr. Howard Johnson in *High Speed Digital Design: A Handbook of Black Magic* (Prentice Hall, 1993), multiple small capacitors of equal value are recommended over a single large value capacitor.



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output impedance is the average of two components, the resistances of the pull-up and pull-down devices. When data is held high, SW1 is closed (SW2 is open) and R_P is trimmed until the voltage at the pad equals $OV_{DD}/2$. R_P then becomes the resistance of the pull-up devices. R_P and R_N are designed to be close to each other in value. Then, $Z_0 = (R_P + R_N)/2$.



Figure 45. Driver Impedance Measurement

The value of this resistance and the strength of the driver's current source can be found by making two measurements. First, the output voltage is measured while driving logic 1 without an external differential termination resistor. The measured voltage is $V_1 = R_{source} \times I_{source}$. Second, the output voltage is measured while driving logic 1 with an external precision differential termination resistor of value R_{term} . The measured voltage is $V_2 = (1/(1/R_1 + 1/R_2)) \times I_{source}$. Solving for the output impedance gives $R_{source} = R_{term} \times (V_1/V_2 - 1)$. The drive current is then $I_{source} = V_1/R_{source}$.

Table 65 summarizes the signal impedance targets. The driver impedance are targeted at minimum V_{DD} , nominal OV_{DD} , 105°C.

Impedance	Local Bus, Ethernet, DUART, Control, Configuration, Power Management	PCI	DDR DRAM	Symbol	Unit
R _N	42 Target	25 Target	20 Target	Z ₀	W
R _P	42 Target	25 Target	20 Target	Z ₀	W
Differential	NA	NA	NA	Z _{DIFF}	W

Table 65. Impedance Characteristics

Note: Nominal supply voltages. See Table 1, $T_i = 105^{\circ}C$.

24.6 Configuration Pin Multiplexing

The MPC8323E provides the user with power-on configuration options which can be set through the use of external pull-up or pull-down resistors of 4.7 k Ω on certain output pins (see customer visible configuration pins). These pins are generally used as output only pins in normal operation.